# E · Clattice Semiconductor Corporation - <u>LCMXO2-4000HE-4FTG256C Datasheet</u>



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	206
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-4000he-4ftg256c

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#### Table 1-1. MachXO2™ Family Selection Guide

		XO2-256	XO2-640	XO2-640U <sup>1</sup>	XO2-1200	XO2-1200U <sup>1</sup>	XO2-2000	XO2-2000U1	XO2-4000	XO2-7000
LUTs		256	640	640	1280	1280	2112	2112	4320	6864
Distributed RAM (kbits)		2	5	5	10	10	16	16	34	54
EBR SRAM (kbits)		0	18	64	64	74	74	92	92	240
Number of EBR SR kbits/block)	AM Blocks (9	0	2	7	7	8	8	10	10	26
UFM (kbits)		0	24	64	64	80	80	96	96	256
Device Options:	HC <sup>2</sup>	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
	HE <sup>3</sup>						Yes	Yes	Yes	Yes
	ZE <sup>4</sup>	Yes	Yes		Yes		Yes		Yes	Yes
Number of PLLs		0	0	1	1	1	1	2	2	2
Hardened	I2C	2	2	2	2	2	2	2	2	2
Functions:	SPI	1	1	1	1	1	1	1	1	1
	Timer/Coun- ter	1	1	1	1	1	1	1	1	1
Packages	1					ю				
25-ball WLCSP⁵ (2.5 mm x 2.5 mm,	0.4 mm)				18					
32 QFN <sup>6</sup> (5 mm x 5 mm, 0.5	mm)	21			21					
48 QFN <sup>8, 9</sup> (7 mm x 7 mm, 0.5	mm)	40	40							
49-ball WLCSP <sup>5</sup> (3.2 mm x 3.2 mm,	0.4 mm)						38			
64-ball ucBGA (4 mm x 4 mm, 0.4	mm)	44								
84 QFN <sup>7</sup> (7 mm x 7 mm, 0.5	mm)								68	
100-pin TQFP (14 mm x 14 mm)		55	78		79		79			
132-ball csBGA (8 mm x 8 mm, 0.5	mm)	55	79		104		104		104	
144-pin TQFP (20 mm x 20 mm)				107	107		111		114	114
184-ball csBGA <sup>7</sup> (8 mm x 8 mm, 0.5	mm)								150	
256-ball caBGA (14 mm x 14 mm, 0	.8 mm)						206		206	206
256-ball ftBGA (17 mm x 17 mm, 1	.0 mm)					206	206		206	206
332-ball caBGA (17 mm x 17 mm, 0	.8 mm)								274	278
484-ball ftBGA (23 mm x 23 mm, 1	.0 mm)							278	278	334

1. Ultra high I/O device.

2. High performance with regulator – VCC = 2.5 V, 3.3 V

3. High performance without regulator  $-V_{CC} = 1.2 V$ 4. Low power without regulator  $-V_{CC} = 1.2 V$ 5. WLCSP package only available for ZE devices.

6. 32 QFN package only available for HC and ZE devices.

7. 184 csBGA package only available for HE devices.

8. 48-pin QFN information is 'Advanced'.

9. 48 QFN package only available for HC devices.



 Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
True Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9
Pseudo Dual Port	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18
FIFO	8,192 x 1 4,096 x 2 2,048 x 4 1,024 x 9 512 x 18

#### Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

#### **RAM Initialization and ROM Operation**

If desired, the contents of the RAM can be pre-loaded during device configuration. EBR initialization data can be loaded from the UFM. To maximize the number of UFM bits, initialize the EBRs used in your design to an all-zero pattern. Initializing to an all-zero pattern does not use up UFM bits. MachXO2 devices have been designed such that multiple EBRs share the same initialization memory space if they are initialized to the same pattern.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

#### Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

#### Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 2-8 shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.



#### Figure 2-9. Memory Core Reset



For further information on the sysMEM EBR block, please refer to TN1201, Memory Usage Guide for MachXO2 Devices.

#### EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

#### Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram

Reset	
Clock	
Clock	

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of 1/f<sub>MAX</sub> (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device wake up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 2-10. The reset timing rules apply to the RPReset input versus the RE input and the RST input versus the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs. For more details refer to TN1201, Memory Usage Guide for MachXO2 Devices.

Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.



### Programmable I/O Cells (PIC)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. On the MachXO2 devices, the PIO cells are assembled into groups of four PIO cells called a Programmable I/O Cell or PIC. The PICs are placed on all four sides of the device.

On all the MachXO2 devices, two adjacent PIOs can be combined to provide a complementary output driver pair.

The MachXO2-640U, MachXO2-1200/U and higher density devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. Half of the PIO pairs on the top edge of these devices can be configured as true LVDS transmit pairs. The PIO pairs on the bottom edge of these higher density devices have on-chip differential termination and also provide PCI support.



### PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8.	ΡΙΟ	Signal	List
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Pin Name	I/О Туре	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
DQSR901	Input	DQS shift 90-degree read clock
DQSW90 <sup>1</sup>	Input	DQS shift 90-degree write clock
DDRCLKPOL <sup>1</sup>	Input	DDR input register polarity control signal from DQS
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

1. Available in PIO on right edge only.

#### Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition to this functionality, the input register blocks for the PIOs on the right edge include built-in logic to interface to DDR memory.

Figure 2-12 shows the input register block for the PIOs located on the left, top and bottom edges. Figure 2-13 shows the input register block for the PIOs on the right edge.

#### Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.



### **Output Register Block**

The output register block registers signals from the core of the device before they are passed to the sysIO buffers.

#### Left, Top, Bottom Edges

In SDR mode, D0 feeds one of the flip-flops that then feeds the output. The flip-flop can be configured as a D-type register or latch.

In DDR generic mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the same clock is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-14 shows the output register block on the left, top and bottom edges.

Figure 2-14. MachXO2 Output Register Block Diagram (PIO on the Left, Top and Bottom Edges)



#### **Right Edge**

The output register block on the right edge is a superset of the output register on left, top and bottom edges of the device. In addition to supporting SDR and Generic DDR modes, the output register blocks for PIOs on the right edge include additional logic to support DDR-memory interfaces. Operation of this block is similar to that of the output register block on other edges.

In DDR memory mode, D0 and D1 inputs are fed into registers on the positive edge of the clock. At the next falling edge the registered D1 input is registered into the register Q1. A multiplexer running off the DQSW90 signal is used to switch the mux between the outputs of registers Q0 and Q1 that will then feed the output.

Figure 2-15 shows the output register block on the right edge.



#### Table 2-11. I/O Support Device by Device

	MachXO2-256, MachXO2-640	MachXO2-640U, MachXO2-1200	MachXO2-1200U MachXO2-2000/U, MachXO2-4000, MachXO2-7000	
Number of I/O Banks	4	4	6	
		Single-ended (all I/O banks)	Single-ended (all I/O banks)	
Tupo of Input Pufforo	Single-ended (all I/O banks)	Differential Receivers (all I/O	Differential Receivers (all I/O	
	Differential Receivers (all I/O banks)	Differential input termination (bottom side)	Differential input termination (bottom side)	
Turses of Output Duffers	Single-ended buffers with	Single-ended buffers with complementary outputs (all I/O banks)	Single-ended buffers with complementary outputs (all I/O banks)	
Types of Output Bullers	banks)	Differential buffers with true LVDS outputs (50% on top side)	Differential buffers with true LVDS outputs (50% on top side)	
Differential Output Emulation Capability	All I/O banks	All I/O banks	All I/O banks	
PCI Clamp Support	No	Clamp on bottom side only	Clamp on bottom side only	

#### Table 2-12. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	3.3 V	2.5 V	1.8 V	1.5	1.2 V
Single-Ended Interfaces					
LVTTL	✓	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	
LVCMOS33	✓	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	
LVCMOS25	<b>√</b> <sup>2</sup>	✓	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	
LVCMOS18	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	✓	<b>√</b> <sup>2</sup>	
LVCMOS15	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	~	<b>√</b> <sup>2</sup>
LVCMOS12	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	<b>√</b> <sup>2</sup>	✓
PCI <sup>1</sup>	✓				
SSTL18 (Class I, Class II)	✓	✓	✓		
SSTL25 (Class I, Class II)	✓	✓			
HSTL18 (Class I, Class II)	✓	✓	✓		
Differential Interfaces		•			
LVDS	✓	✓			
BLVDS, MVDS, LVPECL, RSDS	✓	✓			
MIPI <sup>3</sup>	✓	✓			
Differential SSTL18 Class I, II	✓	✓	✓		
Differential SSTL25 Class I, II	✓	✓			
Differential HSTL18 Class I, II	✓	~	✓		

1. Bottom banks of MachXO2-640U, MachXO2-1200/U and higher density devices only.

2. Reduced functionality. Refer to TN1202, MachXO2 sysIO Usage Guide for more detail.

3. These interfaces can be emulated with external resistors in all devices.



Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and referenced and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors VCC levels. In the event of unsafe $V_{CC}$ drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Referenced and differential I/O buffers (used to implement standards such as HSTL, SSTL and LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1198, Power Estimation and Management for MachXO2 Devices.

### Power On Reset

MachXO2 devices have power-on reset circuitry to monitor  $V_{CCINT}$  and  $V_{CCIO}$  voltage levels during power-up and operation. At power-up, the POR circuitry monitors  $V_{CCINT}$  and  $V_{CCIO0}$  (controls configuration) voltage levels. It then triggers download from the on-chip configuration Flash memory after reaching the  $V_{PORUP}$  level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For devices without voltage regulators (ZE and HE devices),  $V_{CCINT}$  is the same as the  $V_{CC}$  supply voltage. For devices with voltage regulators (HC devices),  $V_{CCINT}$  is regulated from the  $V_{CC}$  supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as Flash Download Time (t<sub>REFRESH</sub>) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tristate. I/Os are released to user functionality once the device has finished configuration. Note that for HC devices, a separate POR circuit monitors external  $V_{CC}$  voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor  $V_{CCINT}$  levels. If  $V_{CCINT}$  drops below  $V_{PORDNBG}$  level (with the bandgap circuitry switched on) or below  $V_{PORDNSRAM}$  level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the  $V_{CCINT}$  and  $V_{CCIO}$  voltage levels.  $V_{PORDNBG}$  and  $V_{PORDNSRAM}$  are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once a ZE or HE device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a minimal, low power POR circuit is still operational (this corresponds to the  $V_{PORDNSRAM}$  reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the  $V_{CC}$  supply dropping below  $V_{CC}$  (min) they should not shut down the bandgap or POR circuit.



# MachXO2 Family Data Sheet DC and Switching Characteristics

#### March 2017

#### Data Sheet DS1035

### Absolute Maximum Ratings<sup>1, 2, 3</sup>

	MachXO2 ZE/HE (1.2 V)	MachXO2 HC (2.5 V / 3.3 V)
Supply Voltage V <sub>CC</sub>	–0.5 V to 1.32 V	0.5 V to 3.75 V
Output Supply Voltage V <sub>CCIO</sub>	–0.5 V to 3.75 V	0.5 V to 3.75 V
I/O Tri-state Voltage Applied <sup>4, 5</sup>	–0.5 V to 3.75 V	0.5 V to 3.75 V
Dedicated Input Voltage Applied <sup>4</sup>	–0.5 V to 3.75 V	0.5 V to 3.75 V
Storage Temperature (Ambient)	–55 °C to 125 °C	–55 °C to 125 °C
Junction Temperature $(T_1)$	–40 °C to 125 °C	–40 °C to 125 °C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V<sub>IHMAX</sub> + 2) volts is permitted for a duration of <20 ns.

5. The dual function  $I^2C$  pins SCL and SDA are limited to -0.25 V to 3.75 V or to -0.3 V with a duration of <20 ns.

### **Recommended Operating Conditions**<sup>1</sup>

Symbol	Parameter	Min.	Max.	Units
V = = <sup>1</sup>	Core Supply Voltage for 1.2 V Devices	1.14	1.26	V
V <sub>CC</sub> .	Core Supply Voltage for 2.5 V / 3.3 V Devices	2.375	3.6	V
V <sub>CCIO</sub> <sup>1, 2, 3</sup>	I/O Driver Supply Voltage	1.14	3.6	V
t <sub>JCOM</sub>	Junction Temperature Commercial Operation	0	85	°C
t <sub>JIND</sub>	Junction Temperature Industrial Operation	-40	100	°C

1. Like power supplies must be tied together. For example, if  $V_{CCIO}$  and  $V_{CC}$  are both the same voltage, they must also be the same supply.

2. See recommended voltages by I/O standard in subsequent table.

3. V<sub>CCIO</sub> pins of unused I/O banks should be connected to the V<sub>CC</sub> power supply on boards.

### Power Supply Ramp Rates<sup>1</sup>

Symbol	Parameter	Min.	Тур.	Max.	Units
t <sub>RAMP</sub>	Power supply ramp rates for all power supplies.	0.01		100	V/ms

1. Assumes monotonic ramp rates.

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### Power-On-Reset Voltage Levels<sup>1, 2, 3, 4, 5</sup>

Symbol	Parameter	Min.	Тур.	Max.	Units
V <sub>PORUP</sub>	Power-On-Reset ramp up trip point (band gap based circuit monitoring $V_{CCINT}$ and $V_{CCIO0})$	0.9	_	1.06	V
V <sub>PORUPEXT</sub>	Power-On-Reset ramp up trip point (band gap based circuit monitoring external $V_{CC}$ power supply)	1.5	_	2.1	V
V <sub>PORDNBG</sub>	Power-On-Reset ramp down trip point (band gap based circuit monitoring $V_{CCINT})$	0.75	_	0.93	V
V <sub>PORDNBGEXT</sub>	Power-On-Reset ramp down trip point (band gap based circuit monitoring $\mathrm{V}_{\mathrm{CC}}$ )	0.98	_	1.33	V
V <sub>PORDNSRAM</sub>	Power-On-Reset ramp down trip point (SRAM based circuit monitoring $V_{\mbox{CCINT}}$ )	-	0.6	_	V
V <sub>PORDNSRAMEXT</sub>	Power-On-Reset ramp down trip point (SRAM based circuit monitoring $V_{CC}$ )	_	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.

2. For devices without voltage regulators V<sub>CCINT</sub> is the same as the V<sub>CC</sub> supply voltage. For devices with voltage regulators, V<sub>CCINT</sub> is regulated from the V<sub>CC</sub> supply voltage.

3. Note that V<sub>PORUP</sub> (min.) and V<sub>PORDNBG</sub> (max.) are in different process corners. For any given process corner V<sub>PORDNBG</sub> (max.) is always 12.0 mV below V<sub>PORUP</sub> (min.).

4. V<sub>PORUPEXT</sub> is for HC devices only. In these devices a separate POR circuit monitors the external V<sub>CC</sub> power supply.

5. V<sub>CCIO0</sub> does not have a Power-On-Reset ramp down trip point. V<sub>CCIO0</sub> must remain within the Recommended Operating Conditions to ensure proper operation.

### **Programming/Erase Specifications**

Symbol	Parameter	Min.	Max. <sup>1</sup>	Units
	Flash Programming cycles per t <sub>RETENTION</sub>	—	10,000	Cycles
PROGCYC	Flash functional programming cycles	—	100,000	Oycles
t <sub>RETENTION</sub>	Data retention at 100 °C junction temperature	10	—	Voars
	Data retention at 85 °C junction temperature	20	—	leais

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

### Hot Socketing Specifications<sup>1, 2, 3</sup>

$I_{DK}$ Input or I/O leakage Current $0 < V_{IN} < V_{IH}$ (MAX) +/-1000 $\mu$ A	Symbol	Parameter	Condition	Max.	Units
	I <sub>DK</sub>	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μΑ

1. Insensitive to sequence of  $V_{CC}$  and  $V_{CCIO}$ . However, assumes monotonic rise/fall rates for  $V_{CC}$  and  $V_{CCIO}$ .

2.  $0 < V_{CC} < V_{CC}$  (MAX),  $0 < V_{CCIO} < V_{CCIO}$  (MAX).

3. I<sub>DK</sub> is additive to I<sub>PU</sub>, I<sub>PD</sub> or I<sub>BH</sub>.

### **ESD Performance**

Please refer to the MachXO2 Product Family Qualification Summary for complete qualification data, including ESD performance.



### sysCONFIG Port Timing Specifications

Symbol	Pa	arameter	Min.	Max.	Units				
All Configuration Modes									
t <sub>PRGM</sub>	PROGRAMN low p	oulse accept	55	—	ns				
t <sub>PRGMJ</sub>	PROGRAMN low p	oulse rejection	-	25	ns				
t <sub>INITL</sub>	INITN low time	LCMXO2-256	—	30	μs				
		LCMXO2-640	—	35	μs				
		LCMXO2-640U/ LCMXO2-1200	—	55	μs				
		LCMXO2-1200U/ LCMXO2-2000	-	70	μs				
		LCMXO2-2000U/ LCMXO2-4000	_	105	μs				
		LCMXO2-7000	—	130	μs				
t <sub>DPPINIT</sub>	PROGRAMN low t	o INITN low	—	150	ns				
t <sub>DPPDONE</sub>	PROGRAMN low t	o DONE low	—	150	ns				
t <sub>IODISS</sub>	PROGRAMN low t	o I/O disable	—	120	ns				
Slave SPI			•		•				
f <sub>MAX</sub>	CCLK clock freque	CCLK clock frequency		66	MHz				
t <sub>CCLKH</sub>	CCLK clock pulse	CCLK clock pulse width high		—	ns				
t <sub>CCLKL</sub>	CCLK clock pulse	CCLK clock pulse width low		—	ns				
t <sub>STSU</sub>	CCLK setup time		2	—	ns				
t <sub>STH</sub>	CCLK hold time		0	—	ns				
t <sub>STCO</sub>	CCLK falling edge	to valid output	—	10	ns				
t <sub>STOZ</sub>	CCLK falling edge	to valid disable	—	10	ns				
t <sub>STOV</sub>	CCLK falling edge	to valid enable	—	10	ns				
t <sub>SCS</sub>	Chip select high tir	ne	25	—	ns				
t <sub>SCSS</sub>	Chip select setup t	ime	3	—	ns				
t <sub>SCSH</sub>	Chip select hold tir	ne	3	—	ns				
Master SPI									
f <sub>MAX</sub>	MCLK clock freque	MCLK clock frequency		133	MHz				
t <sub>MCLKH</sub>	MCLK clock pulse	MCLK clock pulse width high		—	ns				
t <sub>MCLKL</sub>	MCLK clock pulse	MCLK clock pulse width low		—	ns				
t <sub>STSU</sub>	MCLK setup time		5	—	ns				
t <sub>STH</sub>	MCLK hold time		1	—	ns				
t <sub>CSSPI</sub>	INITN high to chip	select low	100	200	ns				
t <sub>MCLK</sub>	INITN high to first I	MCLK edge	0.75	1	μs				



### Signal Descriptions (Cont.)

Signal Name	I/O	Descriptions
INITN	I/O	Open Drain pin. Indicates the FPGA is ready to be configured. During configuration, or when reserved as INITn in user mode, this pin has an active pull-up.
DONE	I/O	Open Drain pin. Indicates that the configuration sequence is complete, and the start-up sequence is in progress. During configuration, or when reserved as DONE in user mode, this pin has an active pull-up.
MCLK/CCLK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA in SPI and SPIm configuration modes.
SN	I	Slave SPI active low chip select input.
CSSPIN	I/O	Master SPI active low chip select output.
SI/SPISI	I/O	Slave SPI serial data input and master SPI serial data output.
SO/SPISO	I/O	Slave SPI serial data output and master SPI serial data input.
SCL	I/O	Slave I <sup>2</sup> C clock input and master I <sup>2</sup> C clock output.
SDA	I/O	Slave I <sup>2</sup> C data input and master I <sup>2</sup> C data output.



	MachXO2-2000						MachXO2-2000U
	49 WLCSP	100 TQFP	132 csBGA	144 TQFP	256 caBGA	256 ftBGA	484 ftBGA
General Purpose I/O per Bank			1				
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
	-		-				
Dual Function I/O	24	31	33	33	33	33	37
High-speed Differential I/O			1				
Bank 0	5	4	8	9	14	14	18
Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups			1				
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484



## MachXO2 Family Data Sheet Ordering Information

March 2017

Data Sheet DS1035

### MachXO2 Part Number Description



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### **Ordering Information**

MachXO2 devices have top-side markings, for commercial and industrial grades, as shown below:



Notes:

- 1. Markings are abbreviated for small packages.
- 2. See PCN 05A-12 for information regarding a change to the top-side mark logo.



Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000ZE-1TG144C	6864	1.2 V	-1	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-2TG144C	6864	1.2 V	-2	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-3TG144C	6864	1.2 V	-3	Halogen-Free TQFP	144	COM
LCMXO2-7000ZE-1BG256C	6864	1.2 V	-1	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-2BG256C	6864	1.2 V	-2	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-3BG256C	6864	1.2 V	-3	Halogen-Free caBGA	256	COM
LCMXO2-7000ZE-1FTG256C	6864	1.2 V	-1	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-2FTG256C	6864	1.2 V	-2	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-3FTG256C	6864	1.2 V	-3	Halogen-Free ftBGA	256	COM
LCMXO2-7000ZE-1BG332C	6864	1.2 V	-1	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-2BG332C	6864	1.2 V	-2	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-3BG332C	6864	1.2 V	-3	Halogen-Free caBGA	332	COM
LCMXO2-7000ZE-1FG484C	6864	1.2 V	-1	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-2FG484C	6864	1.2 V	-2	Halogen-Free fpBGA	484	COM
LCMXO2-7000ZE-3FG484C	6864	1.2 V	-3	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100CR11	1280	1.2 V	-1	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-2TG100CR11	1280	1.2 V	-2	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-3TG100CR11	1280	1.2 V	-3	Halogen-Free TQFP	100	COM
LCMXO2-1200ZE-1MG132CR1 <sup>1</sup>	1280	1.2 V	-1	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-2MG132CR11	1280	1.2 V	-2	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-3MG132CR1 <sup>1</sup>	1280	1.2 V	-3	Halogen-Free csBGA	132	COM
LCMXO2-1200ZE-1TG144CR1 <sup>1</sup>	1280	1.2 V	-1	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-2TG144CR1 <sup>1</sup>	1280	1.2 V	-2	Halogen-Free TQFP	144	COM
LCMXO2-1200ZE-3TG144CR1 <sup>1</sup>	1280	1.2 V	-3	Halogen-Free TQFP	144	COM

1. Specifications for the "LCMXO2-1200ZE-speed package CR1" are the same as the "LCMXO2-1200ZE-speed package C" devices respectively, except as specified in the R1 Device Specifications section of this data sheet.



### Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-256ZE-1SG32I	256	1.2 V	-1	Halogen-Free QFN	32	IND
LCMXO2-256ZE-2SG32I	256	1.2 V	-2	Halogen-Free QFN	32	IND
LCMXO2-256ZE-3SG32I	256	1.2 V	-3	Halogen-Free QFN	32	IND
LCMXO2-256ZE-1UMG64I	256	1.2 V	-1	Halogen-Free ucBGA	64	IND
LCMXO2-256ZE-2UMG64I	256	1.2 V	-2	Halogen-Free ucBGA	64	IND
LCMXO2-256ZE-3UMG64I	256	1.2 V	-3	Halogen-Free ucBGA	64	IND
LCMXO2-256ZE-1TG100I	256	1.2 V	-1	Halogen-Free TQFP	100	IND
LCMXO2-256ZE-2TG100I	256	1.2 V	-2	Halogen-Free TQFP	100	IND
LCMXO2-256ZE-3TG100I	256	1.2 V	-3	Halogen-Free TQFP	100	IND
LCMXO2-256ZE-1MG132I	256	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-256ZE-2MG132I	256	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-256ZE-3MG132I	256	1.2 V	-3	Halogen-Free csBGA	132	IND
						-
Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-640ZE-1TG100I	640	1.2 V	-1	Halogen-Free TQFP	100	IND
LCMXO2-640ZE-2TG100I	640	1.2 V	-2	Halogen-Free TQFP	100	IND
LCMXO2-640ZE-3TG100I	640	1.2 V	-3	Halogen-Free TQFP	100	IND
LCMXO2-640ZE-1MG132I	640	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-640ZE-2MG132I	640	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-640ZE-3MG132I	640	1.2 V	-3	Halogen-Free csBGA	132	IND
	-	- 1	r		1	1
Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1UWG25ITR <sup>1</sup>	1280	1.2 V	-1	Halogen-Free WLCSP	25	IND
LCMXO2-1200ZE-1UWG25ITR50	<sup>3</sup> 1280	1.2 V	-1	Halogen-Free WLCSP	25	IND
LCMXO2-1200ZE-1UWG25ITR1K	<sup>2</sup> 1280	1.2 V	-1	Halogen-Free WLCSP	25	IND
LCMXO2-1200ZE-1SG32I	1280	1.2 V	-1	Halogen-Free QFN	32	IND
LCMXO2-1200ZE-2SG32I	1280	1.2 V	-2	Halogen-Free QFN	32	IND
LCMXO2-1200ZE-3SG32I	1280	1.2 V	-3	Halogen-Free QFN	32	IND
LCMXO2-1200ZE-1TG100I	1280	1.2 V	-1	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-2TG100I	1280	1.2 V	-2	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-3TG100I	1280	1.2 V	-3	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-1MG132I	1280	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-2MG132I	1280	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-3MG132I	1280	1.2 V	-3	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-1TG144I	1280	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-2TG144I	1280	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-3TG144I	1280	1.2 V	-3	Halogen-Free TQFP	144	IND

1. This part number has a tape and reel quantity of 5,000 units with a minimum order quantity of 10,000 units. Order quantities must be in increments of 5,000 units. For example, a 10,000 unit order will be shipped in two reels with one reel containing 5,000 units and the other reel with less than 5,000 units (depending on test yields). Unserviced backlog will be canceled.

2. This part number has a tape and reel quantity of 1,000 units with a minimum order quantity of 1,000. Order quantities must be in increments of 1,000 units. For example, a 5,000 unit order will be shipped as 5 reels of 1000 units each.

3. This part number has a tape and reel quantity of 50 units with a minimum order quantity of 50. Order quantities must be in increments of 50 units. For example, a 1,000 unit order will be shipped as 20 reels of 50 units each.



Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100IR11	1280	1.2 V	-1	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-2TG100IR11	1280	1.2 V	-2	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-3TG100IR11	1280	1.2 V	-3	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-1MG132IR1 <sup>1</sup>	1280	1.2 V	-1	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-2MG132IR1 <sup>1</sup>	1280	1.2 V	-2	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-3MG132IR11	1280	1.2 V	-3	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-1TG144IR11	1280	1.2 V	-1	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-2TG144IR11	1280	1.2 V	-2	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-3TG144IR11	1280	1.2 V	-3	Halogen-Free TQFP	144	IND

1. Specifications for the "LCMXO2-1200ZE-speed package IR1" are the same as the "LCMXO2-1200ZE-speed package I" devices respectively, except as specified in the R1 Device Specifications section of this data sheet.



### **R1 Device Specifications**

The LCMXO2-1200ZE/HC "R1" devices have the same specifications as their Standard (non-R1) counterparts except as listed below. For more details on the R1 to Standard migration refer to AN8086, Designing for Migration from MachXO2-1200-R1 to Standard Non-R1) Devices.

- The User Flash Memory (UFM) cannot be programmed through the internal WISHBONE interface. It can still be programmed through the JTAG/SPI/I<sup>2</sup>C ports.
- The on-chip differential input termination resistor value is higher than intended. It is approximately 200Ω as opposed to the intended 100Ω. It is recommended to use external termination resistors for differential inputs. The on-chip termination resistors can be disabled through Lattice design software.
- Soft Error Detection logic may not produce the correct result when it is run for the first time after configuration. To use this feature, discard the result from the first operation. Subsequent operations will produce the correct result.
- Under certain conditions, IIH exceeds data sheet specifications. The following table provides more details:

Condition	Clamp	Pad Rising IIH Max.	Pad Falling IIH Min.	Steady State Pad High IIH	Steady State Pad Low IIL
VPAD > VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD = VCCIO	ON	10 µA	–10 μA	10 µA	10 µA
VPAD = VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD < VCCIO	OFF	10 µA	–10 μA	10 µA	10 µA

- The user SPI interface does not operate correctly in some situations. During master read access and slave write access, the last byte received does not generate the RRDY interrupt.
- In GDDRX2, GDDRX4 and GDDR71 modes, ECLKSYNC may have a glitch in the output under certain conditions, leading to possible loss of synchronization.
- When using the hard I<sup>2</sup>C IP core, the I<sup>2</sup>C status registers I2C\_1\_SR and I2C\_2\_SR may not update correctly.
- PLL Lock signal will glitch high when coming out of standby. This glitch lasts for about 10 μsec before returning low.
- Dual boot only available on HC devices, requires tying VCC and VCCIO2 to the same 3.3 V or 2.5 V supply.



# MachXO2 Family Data Sheet Supplemental Information

#### April 2012

Data Sheet DS1035

### **For Further Information**

A variety of technical notes for the MachXO2 family are available on the Lattice web site.

- TN1198, Power Estimation and Management for MachXO2 Devices
- TN1199, MachXO2 sysCLOCK PLL Design and Usage Guide
- TN1201, Memory Usage Guide for MachXO2 Devices
- TN1202, MachXO2 sysIO Usage Guide
- TN1203, Implementing High-Speed Interfaces with MachXO2 Devices
- TN1204, MachXO2 Programming and Configuration Usage Guide
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices
- TN1206, MachXO2 SRAM CRC Error Detection Usage Guide
- TN1207, Using TraceID in MachXO2 Devices
- TN1074, PCB Layout Recommendations for BGA Packages
- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology
- AN8086, Designing for Migration from MachXO2-1200-R1 to Standard (non-R1) Devices
- AN8066, Boundary Scan Testability with Lattice sysIO Capability
- MachXO2 Device Pinout Files
- Thermal Management document
- · Lattice design tools

For further information on interface standards, refer to the following web sites:

- JEDEC Standards (LVTTL, LVCMOS, LVDS, DDR, DDR2, LPDDR): www.jedec.org
- PCI: www.pcisig.com

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